

NSM21156DW6T1G

Dual Complementary Transistors

General Purpose PNP Transistor and NPN Transistors with Monolithic Bias Network

NSM21156DW6T1G contains a single PNP transistor and a monolithic bias network NPN transistor with two resistors; a series base resistor and a base-emitter resistor. This device is designed to replace multiple transistors and resistors on customer boards by integrating these components into a single device. NSM21156DW6T1G is housed in a SC-88/SOT-363 package which is ideal for low power surface mount applications in space constrained applications.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Q1: NPN BRT, R1 = R2 = 10 k
- Q2: PNP
- This is a Pb-Free Device

Applications

- Logic Switching
- Amplification
- Driver Circuits
- Interface Circuits

MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted)

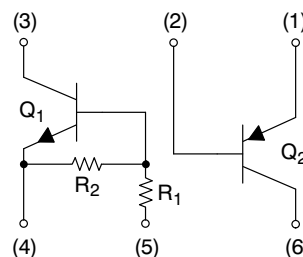
| Rating – Q1 (NPN BRT) | Symbol | Value | Unit |
|--------------------------------|----------------------|-------|------|
| Collector-Base Voltage | V _{CB0} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current | I _C | 100 | mAdc |
| Rating – Q2 (PNP) | Symbol | Value | Unit |
| Collector – Base Voltage | V _{(BR)CBO} | -80 | Vdc |
| Collector – Emitter Voltage | V _{(BR)CEO} | -65 | Vdc |
| Emitter – Base Voltage | V _{(BR)EBO} | -5.0 | Vdc |
| Collector Current – Continuous | I _C | -100 | mAdc |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



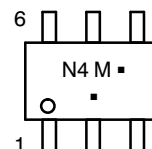
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SC-88/SOT-363
CASE 419B
STYLE 1

MARKING DIAGRAM



N4 = Device Code
M = Date Code*
▪ = Pb-Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------|--------------------|------------------|
| NSM21156DW6T1G | SC-88 (Pb-Free) | 3000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSM21156DW6T1G

THERMAL CHARACTERISTICS

| Characteristic (One Junction Heated) | Symbol | Max | Unit |
|--|-----------------|-------------------------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 180 (Note 1) 1.44 (Note 1) | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 692 (Note 1) | $^\circ\text{C/W}$ |
| Characteristic (Both Junctions Heated) | Symbol | Max | Unit |
| Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 230 1.83 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 544 | $^\circ\text{C/W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

1. FR-4 @ Minimum Pad of 1.45 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS - Q1 NPN BRT ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|---------------|----|---|-----|------|
| Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$) | I_{CBO} | - | - | 100 | nAdc |
| Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$) | I_{CEO} | - | - | 500 | nAdc |
| Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$) | I_{EBO} | - | - | 0.5 | mAdc |
| Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$) | $V_{(BR)CBO}$ | 50 | - | - | Vdc |
| Collector-Emitter Breakdown Voltage (Note 2) ($I_C = 2.0\text{ mA}, I_B = 0$) | $V_{(BR)CEO}$ | 50 | - | - | Vdc |

ON CHARACTERISTICS (Note 2)

| | | | | | |
|---|---------------|-----|-----|------|------------|
| DC Current Gain ($V_{CE} = 10\text{ V}, I_C = 5.0\text{ mA}$) | h_{FE} | 35 | 60 | - | |
| Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$) | $V_{CE(sat)}$ | - | - | 0.25 | Vdc |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$) | V_{OL} | - | - | 0.2 | Vdc |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | - | - | Vdc |
| Input Resistor | R1 | 7.0 | 10 | 13 | k Ω |
| Resistor Ratio | R1/R2 | 0.8 | 1.0 | 1.2 | |

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

NSM21156DW6T1G

ELECTRICAL CHARACTERISTICS - Q2 PNP ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---------------|------|-----|-------------|---------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector - Emitter Breakdown Voltage ($I_C = -10\text{ mA}$) | $V_{(BR)CEO}$ | -65 | - | - | V |
| Collector - Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$) | $V_{(BR)CES}$ | -80 | - | - | V |
| Collector - Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$) | $V_{(BR)CBO}$ | -80 | - | - | V |
| Emitter - Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$) | $V_{(BR)EBO}$ | -5.0 | - | - | V |
| Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$) | I_{CBO} | - | - | -15 -4.0 | nA μA |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|-----------|--------------|----------------|---|
| DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) | h_{FE} | - 220 | 150 290 | - 475 | - |
| Collector - Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{CE(sat)}$ | - - | - - | -0.3 -0.65 | V |
| Base - Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{BE(sat)}$ | - - | -0.7 -0.9 | - - | V |
| Base - Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$) | $V_{BE(on)}$ | -0.6 - | - - | -0.75 -0.82 | V |

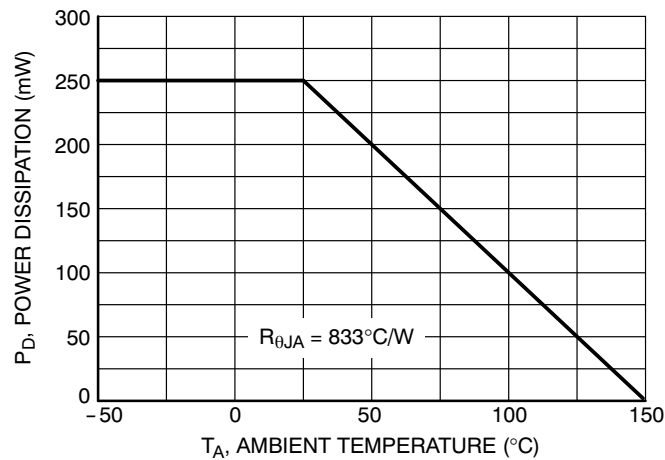


Figure 1. Derating Curve

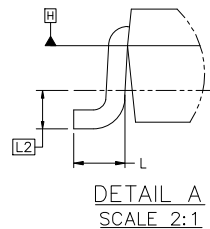
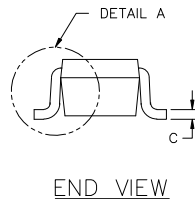
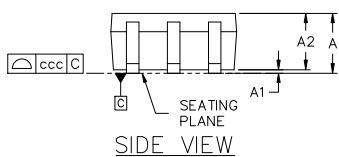
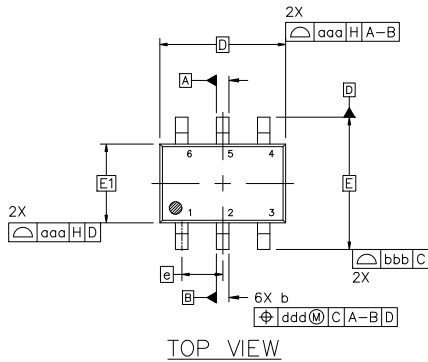


SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

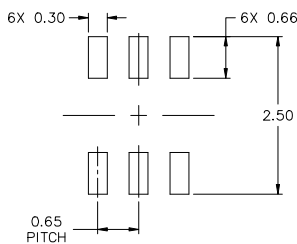
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

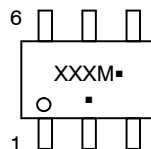


| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.10 |
| A1 | 0.00 | --- | 0.10 |
| A2 | 0.70 | 0.90 | 1.00 |
| b | 0.15 | 0.20 | 0.25 |
| c | 0.08 | 0.15 | 0.22 |
| D | 2.00 BSC | | |
| E | 2.10 BSC | | |
| E1 | 1.25 BSC | | |
| e | 0.65 BSC | | |
| L | 0.26 | 0.36 | 0.46 |
| L2 | 0.15 BSC | | |
| aaa | 0.15 | | |
| bbb | 0.30 | | |
| ccc | 0.10 | | |
| ddd | 0.10 | | |



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

| | | | | | |
|--|--|---|---|---|---|
| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC | STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1 | STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1 | STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1 | STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1 |
| STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF | STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR | STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1 | STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c) | STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C | STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE |
| STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1 | STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 | STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2 | STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE | STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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